COMPLIANT

HALOGEN

FREE



Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt®



PRIMARY CHARACTERISTICS				
I _{F(AV)}	30 A			
V_{R}	650 V			
V _F at I _F	1.4 V			
t _{rr} typ.	33 ns			
T _J max.	175 °C			
Package	2L TO-220AC			
Circuit configuration	Single			

FEATURES

- Hyper fast and soft recovery
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Ultra low V_{F} , soft-switching hyper fast rectifiers optimized for discontinuous (critical) mode (DCM) power factor correction (PFC).

The minimized conduction loss, optimized stored charge and low recovery current minimized the switching losses and reduce over dissipation in the switching element and snubbers.

The device is also intended for use as a freewheeling diode in power supplies and other power switching applications.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Repetitive peak reverse voltage	V_{RRM}		650	V	
Average rectified forward current	I _{F(AV)}	T _C = 120 °C	30	۸	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	210	А	
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	650	ı	-		
Forward voltage V _F		I _F = 30 A	-	1.8	2.1	V	
Forward voltage V _F	I _F = 30 A, T _J = 150 °C	-	1.4	1.6			
Developed lands are assument.	$V_R = V_R$ rated	-	0.02	30			
Reverse leakage current	I _R	T _J = 150 °C, V _R = V _R rated	-	50	300	μΑ	
Junction capacitance	C _T	V _R = 650 V	-	22	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time t _{rr}	T _J = 25 °C	I _F = 1 A dI _F /dt = 100 A/μs V _R = 30 V	-	37	-	ns	
	T _J = 25 °C		-	33	-	113	
	T _J = 125 °C		-	88	-		
Dools woods on a commont	Peak recovery current I _{RRM}	T _J = 25 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 1000 \text{ A/}\mu\text{s}$ $V_R = 400 \text{ V}$	-	18	-	۸
Peak recovery current I _{RRM}		T _J = 125 °C		-	30	-	А
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	450	-	nC
	T _J = 125 °C		-	1350	=	IIC	

THERMAL - MECHANICAL SPECIFICATIONS (T _J = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to case	R _{thJC}		-	1.0	1.3	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	-	0.5	
Weight			-	2.0	-	g
vveignt			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style 2L TO-220AC		ETH	3007	

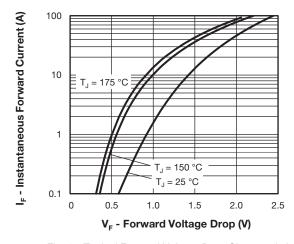


Fig. 1 - Typical Forward Voltage Drop Characteristics

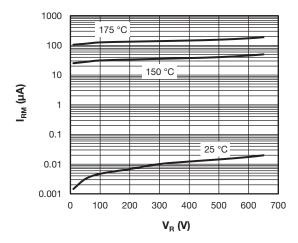


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



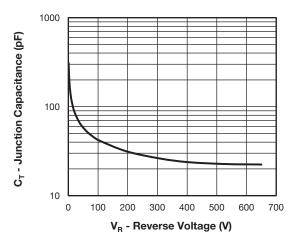


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

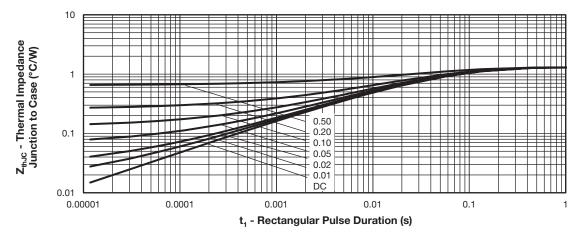


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

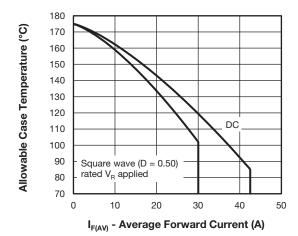


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

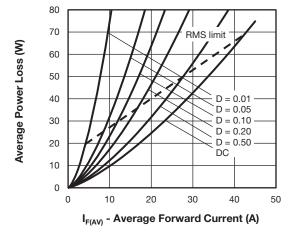
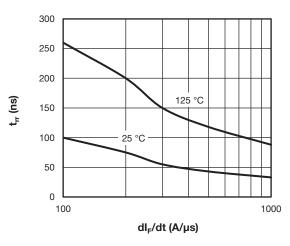


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = rated V_R$

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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

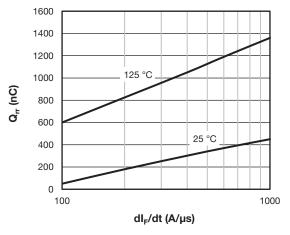
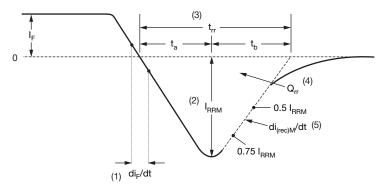


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) ${\rm Q_{rr}}$ area under curve defined by ${\rm t_{rr}}$ and ${\rm I_{RRM}}$

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

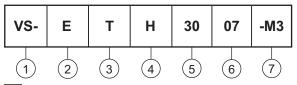
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- E = single diode
- Package:

T = TO-220AC

- H = hyper fast recovery
- 5 Current rating (30 = 30 A)
- 6 Voltage rating (07 = 650 V)
- 7 Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-ETH3007-M3	50	1000	Antistatic plastic tube	

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96156			
Part marking information	www.vishay.com/doc?95391			
SPICE model	www.vishay.com/doc?96531			



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